Miniature Reflective Object Sensor

Product Preview

QRE1114GR

Features

- Phototransistor Output
- No Contact Surface Sensing
- Miniature Package
- Narrow On-State Collector Current

MAXIMUM RATINGS (T_A = 25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
TOPR	Operating Temperature	-40 to +85	°C
Tstg	Storage Temperature	-40 to +90	°C
Tsol-I	Soldering Temperature (Iron) (Notes 2, 3, 4)		
Tsol-F	Soldering Temperature (Flow) (Notes 3, 4)	260 for 10 s	°C

EMITER

I _F	Continuous Forward Current	50	mA	
V_R	Reverse Voltage	5	V	
IFP	Peak Forward Current (Note 5)	1	Α	
P_D	Power Dissipation (Note 1)	75	mW	

SENSOR

VCEO	Collector-Emitter Voltage	30	V	
VECO	Emitter-Collector Voltage	5	٧	
Ic	Collector Current	20	mA	
P_D	Power Dissipation (Note 1)	50	mW	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

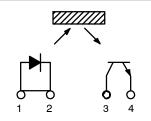
- 1. Derate power dissipation linearly 1.00 mW/°C above 25°C.
- 2. RMA flux is recommended.
- 3. Methanol or isopropyl alcohols are recommended as cleaning agents.
- 4. Soldering iron 1/16" (1.6 mm) from housing.
- 5. Pulse conditions: tp = 100 s; T = 10 ms.

This document contains information on a product under development. ON Semiconductor reserves the right to change or discontinue this product without notice.



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Pin 1: Anode

Pin 2: Cathode Pin 3: Collector

Pin 4: Emitter



ARUSM-313 CASE 100CY

ORDERING INFORMATION

Device	Package	Shipping†
QRE1114GR	Reflective Rectangular (Surface Mount)	1000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_A = 25°C, unless otherwise noted)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
INPUT DIO	DE	•				
V _F	Forward Voltage	I _F = 20 mA	_	1.2	1.6	V
I _R	Reverse Leakage Current	V _R = 5 V	_	-	10	μΑ
PE	Peak Emission Wavelength	I _F = 20 mA	_	940	-	nm
OUTPUT T	RANSISTOR					
I _D	Collector-Emitter Dark Current	I _F = 0 mA, V _{CE} = 20 V	_	-	100	nA
COUPLED						
I _{C(ON)}	On-State Collector Current	I _F = 20 mA, V _{CE} = 5 V (Note 6)	0.30	-	0.60	mA
I _{CX}	Cross-Talk Collector Current	I _F = 20 mA, V _{CE} = 5 V (Note 7)	_	-	1	μΑ
V _{CE(SAT)}	Saturation Voltage	I _F = 20 mA, I _C = 50 μA (Note 6)	_	-	0.3	V
t _r	Rise Time	$V_{CC} = 5 \text{ V}, I_{C(ON)} = 100 \mu\text{A}, R_L = 100 \text{ K}\Omega$	_	20	-	μS
t _f	Fall Time		_	20	-	μs

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

6. Measured using an aluminum alloy mirror at d = 1 mm.

7. No reflective surface at close proximity.

REFLOW PROFILE

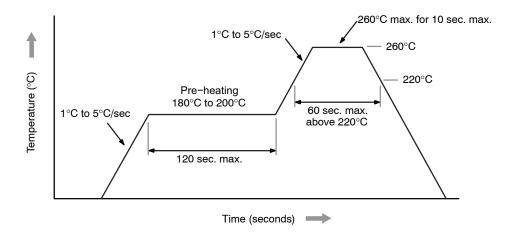


Figure 1. Reflow Profile

TAPING DIMENSIONS

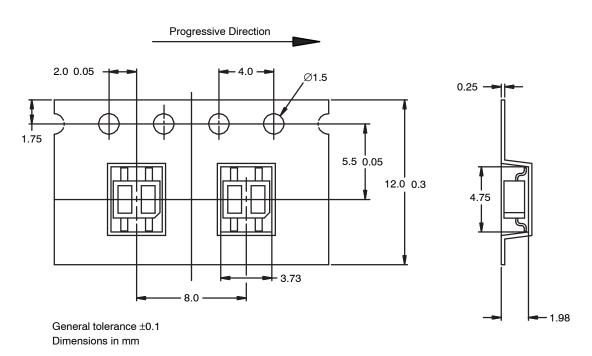


Figure 2. Taping Dimensions for GR Option

REEL DIMENSIONS

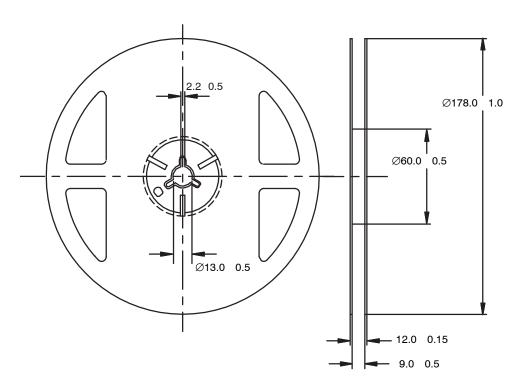
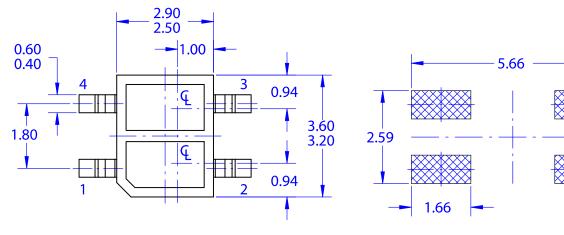


Figure 3. Reel Dimensions

PACKAGE DIMENSIONS

ARUSM-313 / REFLECTIVE RECTANGULAR SURFACE MOUNT

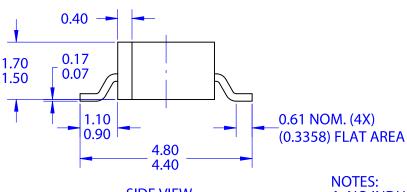
CASE 100CY ISSUE O



TOP VIEW

LAND PATTERN RECOMMENDATION

0.79



SIDE VIEW

A. NO INDUSTRY STANDARD APPLIES

TO THIS PACKAGE

B. ALL DIMENSIONS ARE IN MILLIMETERS ±0.15MM ON ALL

C. TOLERANCE OF **NON-NOMINAL DIMENSIONS**

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